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Substitute for form 1449/PTO PADEM	Complete if Known		
Substitute for form 1449/FTO	Application Number	10/767,102	
INFORMATION DISCLOSURE	Filing Date	01/29/2004	
STATEMENT BY APPLICANT	First Named Inventor	Golovchenko	
	Art Unit	1797	
(Use as many sheets as necessary)	Examiner Name	Brian J. Sines	
Sheet 1 of 1	Attorney Docket Number	HVD2160	

NON PATENT LITERATURE DOCUMENTS Examiner Initials* No.¹ Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. Li et al., "Quantized tunneling current in the metallic nanogaps formed by electrodeposition and etching," Applied Physics Letters, V. 77, N. 24, pp. 3995-3997, December 11, 2000. HE et al., "Electrochemical fabrication of atomically thin metallic wires and electrodes separated with molecular-scale gaps," Jnl. of Electroanalytical Chemistry, V. 522, pp. 167-172, 2002. BOUSSAAD et al., "Atom-size gaps and contacts between electrodes fabricated with a self-terminated electrochemical method," Applied Physics Letters., V. 80, N. 13, pp. 2398-2400, April 1, 2002.				
Initials* No. 1 the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where publisher and etching, "Applied Physics Letters, V. 77, N. 24, pp. 3995-3997, December 11, 2000. HE et al., "Electrochemical fabrication of atomically thin metallic wires and electrodes separated with molecular-scale gaps," Jnl. of Electroanalytical Chemistry, V. 522, pp. 167-172, 2002. BOUSSAAD et al., "Atom-size gaps and contacts between electrodes fabricated with a self-terminated electrochemical method," Applied Physics Letters., V. 80, N. 13, pp. 2398-2400, April 1, 2002.			NON PATENT LITERATURE DOCUMENTS	
B1 and etching," Applied Physics Letters, V. 77, N. 24, pp. 3995-3997, December 11, 2000. B2 HE et al., "Electrochemical fabrication of atomically thin metallic wires and electrodes separated with molecular-scale gaps," Jnl. of Electroanalytical Chemistry, V. 522, pp. 167-172, 2002. B3 BOUSSAAD et al., "Atom-size gaps and contacts between electrodes fabricated with a self-terminated electrochemical method," Applied Physics Letters., V. 80, N. 13, pp. 2398-2400, April 1, 2002.	Examiner Initials*	Cite No. ¹	the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue	T ²
B2 with molecular-scale gaps," Jnl. of Electroanalytical Chemistry, V. 522, pp. 167-172, 2002. B3 B0USSAAD et al., "Atom-size gaps and contacts between electrodes fabricated with a self-terminated electrochemical method," Applied Physics Letters., V. 80, N. 13, pp. 2398-2400, April 1, 2002.		B1	LI et al., "Quantized tunneling current in the metallic nanogaps formed by electrodeposition and etching," Applied Physics Letters, V. 77, N. 24, pp. 3995-3997, December 11, 2000.	
electrochemical method," Applied Physics Letters., V. 80, N. 13, pp. 2398-2400, April 1, 2002.		B2	HE et al., "Electrochemical fabrication of atomically thin metallic wires and electrodes separated with molecular-scale gaps," Jnl. of Electroanalytical Chemistry, V. 522, pp. 167-172, 2002.	
		В3	BOUSSAAD et al., "Atom-size gaps and contacts between electrodes fabricated with a self-terminated electrochemical method," Applied Physics Letters., V. 80, N. 13, pp. 2398-2400, April 1, 2002.	
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